



# **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

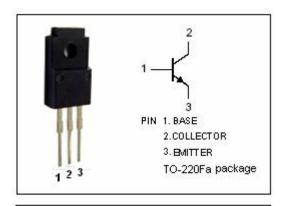
- · Collector-Emitter Breakdown Voltage
  - : V<sub>(BR)CEO</sub>= 150V(Min)
- High Collector Power Dissipation
- · Complement to Type 2SB940
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

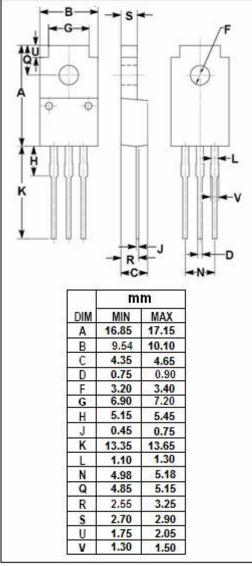
### **APPLICATIONS**

 Designed for power amplifications and TV vertical deflection output applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
Vсво	Collector-Base Voltage	200	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	150	V	
V <sub>ЕВО</sub>	Emitter-Base Voltage	6	V	
lc	Collector Current-Continuous	2	Α	
Ісм	Collector Current-Peak	3	Α	
P <sub>C</sub>	Total Power Dissipation @ T <sub>a</sub> =25℃	2	W	
	Total Power Dissipation @ Tc=25°C	30	VV	
TJ	Junction Temperature	erature 150		
T <sub>stg</sub>	Storage Temperature Range -55~150		$^{\circ}$	







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2SD1264

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA; I <sub>B</sub> = 0	150			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 50 μ A; I <sub>E</sub> = 0	200			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 100 μ A; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.5A; I <sub>B</sub> = 50mA			1.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 0.4A; V <sub>CE</sub> = 10V			1.0	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 200V; I <sub>E</sub> = 0			50	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			50	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.15A; V <sub>CE</sub> = 10V	60		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 0.4A; V <sub>CE</sub> = 10V	50			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V		20		MHz

### ♦ h<sub>FE-1</sub> Classifications

Q	Р
60-140	100-240

### **NOTICE:**

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